Program at a Glance

Date	Jun. 3 (Sun)	Jun. 4 (Mon)			Jun. 5 (Tue)			Jun. 6 (Wed)			Jun. 7 (Thu)			Jun. 8 (Fri)		
Room		Noh Theatre	Room 1&2	Room 3&4	Noh Theatre	Room 1&2	Room 3&4	Noh Theatre	Room 1&2	Room 3&4	Noh Theatre	Room 1&2	Room 3&4	Noh Theatre	Room 1&2	Room 3&4
8:00								Shikayose								
8:30		Registration			Registration			Registration			Registration			Registration		
9:00		Opening			5A-1 Plenary II *Mishra Kunert*			6A-1 AlGaN-Based LEDs	6A-2 III-V Devices on Group IV Substrates		7A-1 Plenary III *Matsuoka Zettler*			8A-1 Nitride LEDs	8A-2 III-V Nanowires	
10:00		4A-1 Plenary I *Amano Samuelson*														
11:00		Break			Break			Break			Break			Break		
12:00		4B-1 Fundamental Nitride Growth	4B-2 III-V Devices and Growth	4B-3 2D Materials	5B-1 GaN Electric Devices	5B-2 AlGaN-Based UV Devices	5B-3 Quantum Dots	6B-1 Growth of AlN and AlGaN	6B-2 Growth of III-V on Si		7B-1 Nitride Lasers	7B-2 In-Situ Analysis	7B-3 Advanced Equipment and Growth Technology	8B-1 Late News Plenary IV *Dupuis*		
13:00		Lunch			Lunch			Excursion			Lunch			Closing		
14:00		4C-1 Nitride Optical Devices (New Applications)	4C-2 Patterned Growth		5C-1 Growth of InN and InGaN	5C-2 Oxide Semiconductors	5C-3 Photonic Devices				7C-1 Advanced Nitride Growth	7C-2 BN Growth and Characterization	7C-3 Characterization			
15:00	Registration															
16:00		Break			P1 Poster Session 1						P2 Poster Session 2					
17:00		4D-1 Material Improvement for Nitride Electric Devices	4D-2 Modeling of MOVPE		Gagaku Concert											
18:00	Welcome Reception				Light meal											
19:00						5E-2 GaN Power Devices - Future Directions from the Viewpoint of Growth	5E-3 History and Future of MOVPE Equipment				Banquet					
20:00																